

**Silicon NPN Power Transistors**

**2N5466 2N5467**

**DESCRIPTION**

- With TO-3 package
- High-voltage capability
- Fast switching speeds
- Low collector saturation voltage

**APPLICATIONS**

- They are intended for use in off-line power supplies ,inverter and converter circuits

**PINNING**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

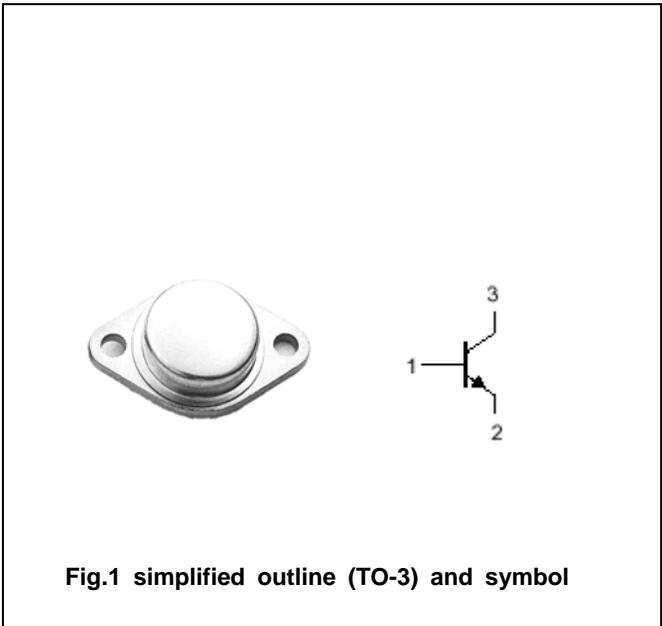


Fig.1 simplified outline (TO-3) and symbol

**Absolute maximum ratings(Ta=°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2N5466	500	V
		2N5467	700	
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		3	A
I <sub>CM</sub>	Collector current-peak		5	A
I <sub>B</sub>	Base current		1	A
P <sub>D</sub>	Total Power Dissipation	T <sub>C</sub> =25°C	140	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~200	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-c</sub>	Thermal resistance junction to case	1.48	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.2A ; I <sub>B</sub> =0	400			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.4A			2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.4A			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =ratedV <sub>CB</sub> O; I <sub>E</sub> =0			1.0	mA
I <sub>CEV</sub>	Collector cut-off current	V <sub>CE</sub> =ratedV <sub>CE</sub> O; V <sub>BE(off)</sub> =1.5V T <sub>C</sub> =125°C			1.0 5.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =4V	15		45	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =2A ; V <sub>CE</sub> =4V	8			
f <sub>T</sub>	Transistion frequency	I <sub>C</sub> =1A ; V <sub>CE</sub> =10V;f=1MHz	2.5			MHz

